

EMIPAK 2B PressFit Power Module

3-Levels Half Bridge Inverter Stage, 150 A



EMIPAK-2B
(package example)

PRIMARY CHARACTERISTICS

Q1 to Q4 IGBT	
V_{CES}	650 V
$V_{CE(on)}$ typical at $I_C = 150$ A	1.70 V
I_C at $T_C = 82$ °C	150 A
Speed	8 kHz to 30 kHz
Package	EMIPAK 2B
Circuit configuration	3-levels half bridge inverter stage

FEATURES

- Trench IGBT technology
- FRED Pt® clamping diodes
- PressFit pins technology
- Exposed Al_2O_3 substrate with low thermal resistance
- Short circuit rated
- Square RBSOA
- Integrated thermistor
- Low internal inductances
- Low switching loss
- PressFit pins locking technology. Patent # US.263.820 B2
- UL approved file E78996 
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT

DESCRIPTION

VS-ETF150Y65N is an integrated solution for a multi level inverter stage in a single package. The EMIPAK 2B package is easy to use thanks to the PressFit pins and the exposed substrate provides improved thermal performance. The optimized layout also helps to minimize stray parameters, allowing for better EMI performance.

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Operating junction temperature	T _J		175	°C
Storage temperature range	T _{Stg}		-40 to +150	
RMS isolation voltage	V _{ISOL}	T _J = 25 °C, all terminals shorted, f = 50 Hz, t = 1 s	3500	V
Q1 to Q4 IGBT				
Collector to emitter voltage	V _{CES}		650	V
Gate to emitter voltage	V _{GES}		20	
Pulsed collector current	I _{CM}		450	A
Clamped inductive load current	I _{LM}		180	
Continuous collector current	I _C	T _C = 25 °C	201	A
		T _C = 60 °C	171	
		T _{SINK} = 60 °C	77	
Power dissipation	P _D	T _C = 25 °C	600	W
		T _C = 60 °C	460	
D5 - D6 CLAMPING DIODE				
Repetitive peak reverse voltage	V _{RRM}		650	V
Single pulse forward current	I _{FSM}	10 ms sine or 6 ms rectangular pulse, T _J = 25 °C	750	A
Diode continuous forward current	I _F	T _C = 25 °C	161	
		T _C = 60 °C	140	
		T _{SINK} = 60 °C	74	
Power dissipation	P _D	T _C = 25 °C	319	W
		T _C = 60 °C	245	

PATENT(S): www.vishay.com/patents

This Vishay product is protected by one or more United States and International patents.


ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
D1 - D2 - D3 - D4 AP DIODE				
Single pulse forward current	I_{FSM}	10 ms sine or 6 ms rectangular pulse, $T_J = 25\text{ }^{\circ}\text{C}$	500	A
Diode continuous forward current	I_F	$T_C = 25\text{ }^{\circ}\text{C}$	102	
		$T_C = 60\text{ }^{\circ}\text{C}$	92	
		$T_{SINK} = 60\text{ }^{\circ}\text{C}$	57	
Power dissipation	P_D	$T_C = 25\text{ }^{\circ}\text{C}$	238	W
		$T_C = 60\text{ }^{\circ}\text{C}$	182	

Notes

- Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur
- (1) $V_{CC} = 325\text{ V}$, $V_{GE} = 15\text{ V}$, $L = 500\text{ }\mu\text{H}$, $R_g = 4.7\text{ }\Omega$, $T_J = 175\text{ }^{\circ}\text{C}$

ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Q1 to Q4 IGBT						
Collector to emitter breakdown voltage	BV _{CES}	V _{GE} = 0 V, I _C = 100 μA	650	-	-	V
Collector to emitter voltage	V _{CE(on)}	V _{GE} = 15 V, I _C = 150 A	-	1.70	2.17	
		V _{GE} = 15 V, I _C = 150 A, T _J = 125 °C	-	1.95	-	
Gate threshold voltage	V _{GE(th)}	V _{CE} = V _{GE} , I _C = 5.0 mA	5.0	6.0	8.4	
Temperature coefficient of threshold voltage	ΔV _{GE(th)} /ΔT _J	V _{CE} = V _{GE} , I _C = 1.0 mA (25 °C to 125 °C)	-	-18	-	mV/°C
Forward transconductance	g _{fe}	V _{CE} = 20 V, I _C = 150 A	-	102	-	S
Transfer characteristics	V _{GE}	V _{CE} = 20 V, I _C = 150 A	-	10.2	-	V
Zero gate voltage collector current	I _{CES}	V _{GE} = 0 V, V _{CE} = 650 V	-	0.1	100	μA
		V _{GE} = 0 V, V _{CE} = 650 V, T _J = 125 °C	-	130	-	
Gate to emitter leakage current	I _{GES}	V _{GE} = ± 20 V, V _{CE} = 0 V	-	-	± 600	nA
D5 - D6 CLAMPING DIODE						
Cathode to anode blocking voltage	V _{BR}	I _R = 500 μA	650	-	-	V
Forward voltage drop	V _{FM}	I _F = 100 A	-	1.64	2.2	
		I _F = 100 A, T _J = 125 °C	-	1.35	-	
Reverse leakage current	I _{RM}	V _R = 650 V	-	0.3	100	μA
		V _R = 650 V, T _J = 125 °C	-	100	-	
D1 - D2 - D3 - D4 AP DIODE						
Forward voltage drop	V _{FM}	I _F = 100 A	-	2.1	2.9	V
		I _F = 100 A, T _J = 125 °C	-	1.64	-	

SWITCHING CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Q1 to Q4 IGBT						
Total gate charge (turn-on)	Q_g	$I_C = 150\text{ A}$ $V_{CC} = 400\text{ V}$ $V_{GE} = 15\text{ V}$	-	310	-	nC
Gate to emitter charge (turn-on)	Q_{ge}		-	95	-	
Gate to collector charge (turn-on)	Q_{gc}		-	130	-	
Input capacitance	C_{ies}	$V_{GE} = 0\text{ V}$ $V_{CC} = 30\text{ V}$ $f = 1\text{ MHz}$	-	9900	-	pF
Output capacitance	C_{oes}		-	460	-	
Reverse transfer capacitance	C_{res}		-	250	-	



SWITCHING CHARACTERISTICS (T _J = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Q1 and Q4 IGBT with D5 and D6 CLAMP DIODE							
Turn-on switching loss	E _{on}	I _C = 150 A V _{CC} = 325 V V _{GE} = 15 V R _g = 4.7 Ω L = 500 μH ⁽¹⁾	-	0.69	-	mJ	
Turn-off switching loss	E _{off}		-	3.4	-		
Total switching loss	E _{tot}		-	4.1	-		
Turn-on delay time	t _{d(on)}		I _C = 150 A V _{CC} = 325 V V _{GE} = 15 V R _g = 4.7 Ω L = 500 μH T _J = 125 °C ⁽¹⁾	-	161	-	ns
Rise time	t _r			-	108	-	
Turn-off delay time	t _{d(off)}			-	139	-	
Fall time	t _f			-	91	-	
Turn-on switching loss	E _{on}	I _C = 150 A V _{CC} = 325 V V _{GE} = 15 V R _g = 4.7 Ω L = 500 μH T _J = 125 °C ⁽¹⁾	-	0.9	-	mJ	
Turn-off switching loss	E _{off}		-	4.2	-		
Total switching loss	E _{tot}		-	5.1	-		
Turn-on delay time	t _{d(on)}		I _C = 150 A V _{CC} = 325 V V _{GE} = 15 V R _g = 4.7 Ω L = 500 μH T _J = 125 °C ⁽¹⁾	-	160	-	ns
Rise time	t _r			-	109	-	
Turn-off delay time	t _{d(off)}			-	150	-	
Fall time	t _f			-	97	-	
Q2 and Q3 IGBT with D2 and D3 AP DIODE							
Turn-on switching loss	E _{on}	I _C = 150 A V _{CC} = 325 V V _{GE} = 15 V R _g = 4.7 Ω L = 500 μH ⁽¹⁾	-	0.8	-	mJ	
Turn-off switching loss	E _{off}		-	4.0	-		
Total switching loss	E _{tot}		-	4.8	-		
Turn-on delay time	t _{d(on)}		I _C = 150 A V _{CC} = 325 V V _{GE} = 15 V R _g = 4.7 Ω L = 500 μH T _J = 125 °C ⁽¹⁾	-	144	-	ns
Rise time	t _r			-	117	-	
Turn-off delay time	t _{d(off)}			-	144	-	
Fall time	t _f			-	98	-	
Turn-on switching loss	E _{on}	I _C = 150 A V _{CC} = 325 V V _{GE} = 15 V R _g = 4.7 Ω L = 500 μH T _J = 125 °C ⁽¹⁾	-	0.98	-	mJ	
Turn-off switching loss	E _{off}		-	4.7	-		
Total switching loss	E _{tot}		-	5.7	-		
Turn-on delay time	t _{d(on)}		I _C = 150 A V _{CC} = 325 V V _{GE} = 15 V R _g = 4.7 Ω L = 500 μH T _J = 125 °C ⁽¹⁾	-	166	-	ns
Rise time	t _r			-	120	-	
Turn-off delay time	t _{d(off)}			-	153	-	
Fall time	t _f			-	106	-	
Reverse bias safe operating area	RBSOA	T _J = 175 °C, I _C = 180 A, V _{CC} = 325 V, V _P = 650 V, R _g = 4.7 Ω, V _{GE} = 15 V to 0 V	Fullsquare				
Short circuit safe operating area	SCSOA	R _g = 5.0 Ω, V _{CC} = 400 V, V _P = 600 V, V _{GE} = 15 V to 0, T _J = 150 °C	-	-	5.5	μs	
D5 - D6 CLAMPING DIODE							
Diode reverse recovery time	t _{rr}	V _R = 200 V I _F = 50 A dI/dt = 500 A/μs	-	78	-	ns	
Diode peak reverse current	I _{rr}		-	11	-	A	
Diode recovery charge	Q _{rr}		-	433	-	nC	
Diode reverse recovery time	t _{rr}	V _R = 200 V I _F = 50 A dI/dt = 500 A/μs, T _J = 125 °C	-	155	-	ns	
Diode peak reverse current	I _{rr}		-	28	-	A	
Diode recovery charge	Q _{rr}		-	2150	-	nC	
D1 - D2 - D3 - D4 AP DIODE							
Diode reverse recovery time	t _{rr}	V _R = 200 V I _F = 50 A dI/dt = 500 A/μs	-	82	-	ns	
Diode peak reverse current	I _{rr}		-	11	-	A	
Diode recovery charge	Q _{rr}		-	363	-	nC	
Diode reverse recovery time	t _{rr}	V _R = 200 V I _F = 50 A dI/dt = 500 A/μs, T _J = 125 °C	-	134	-	ns	
Diode peak reverse current	I _{rr}		-	22	-	A	
Diode recovery charge	Q _{rr}		-	1500	-	nC	

Note⁽¹⁾ Energy losses include "tail" and diode reverse recovery

INTERNAL NTC - THERMISTOR SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	UNITS
Resistance	R25	$T_J = 25\text{ }^{\circ}\text{C}$	$5000 \pm 5\%$	Ω
	R125	$T_J = 100\text{ }^{\circ}\text{C}$	$493 \pm 5\%$	
B-constant	B	$R_2 = R_{25} \exp. [B_{25/50} (1/T_2 - 1/(298.15\text{ K}))]$	$3375 \pm 5\%$	K
Temperature range			-40 to +125	$^{\circ}\text{C}$
Maximum operating temperature			220	
Dissipation constant			2	mW/ $^{\circ}\text{C}$
Thermal time constant			8	s

THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
Q1 to Q4 IGBT - junction to case thermal resistance (per switch)	R_{thJC}	-	-	0.25	$^{\circ}\text{C/W}$
D5 - D6 clamping diode - junction to case thermal resistance (per diode)		-	-	0.47	
D1 - D2 - D3 - D4 AP diode - junction to case thermal resistance (per diode)		-	-	0.63	
Q1 to Q4 IGBT - case to sink thermal resistance (per switch)	$R_{thCS}^{(1)}$	-	0.62	-	
D5 - D6 clamping diode - case to sink thermal resistance (per diode)		-	0.7	-	
D1 - D2 - D3 - D4 AP diode - case to sink thermal resistance (per diode)		-	0.7	-	
Case to sink thermal resistance per module		-	0.1	-	
Mounting torque (M4)		2	-	3	Nm
Weight		-	45	-	g

Note

(1) Mounting surface flat, smooth, and greased

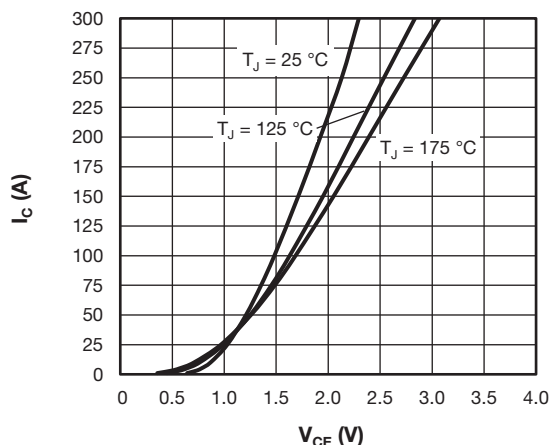


Fig. 1 - I_C vs. V_{CE} ,
Typical Q1 to Q4 Trench IGBT Output Characteristics,
 $V_{GE} = 15\text{ V}$

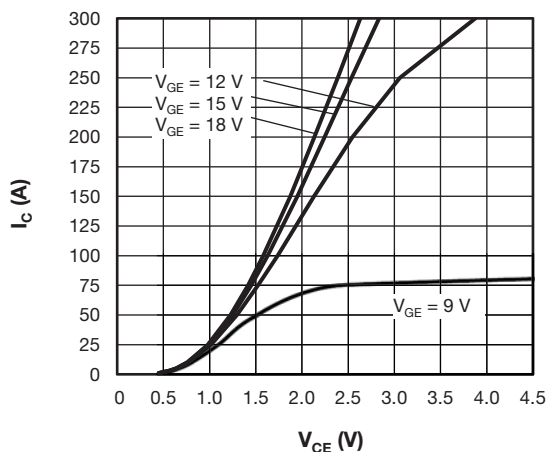


Fig. 2 - I_C vs. V_{CE}
Typical Q1 to Q4 Trench IGBT Output Characteristics,
 $T_J = 125\text{ }^{\circ}\text{C}$

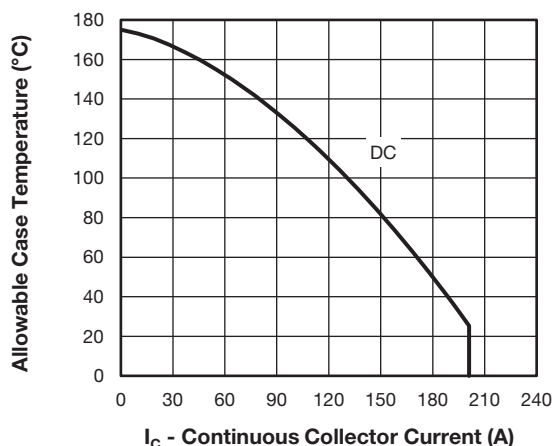


Fig. 3 - Allowable Case Temperature vs. Continuous Collector Current, Maximum Q1 to Q4 Trench IGBT Continuous Collector Current vs. Case Temperature

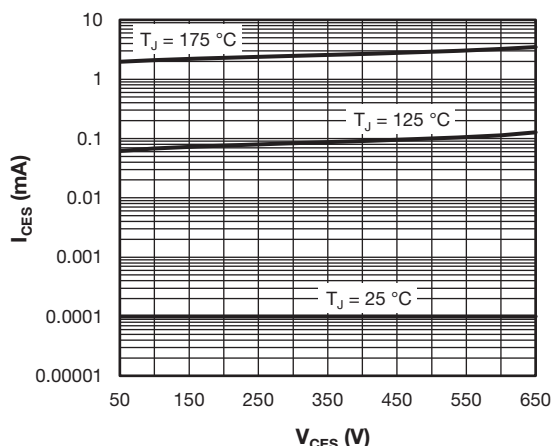


Fig. 6 - I_{CES} vs V_{CES}
Typical Q1 to Q4 Trench IGBT Zero Gate Voltage Collector Current

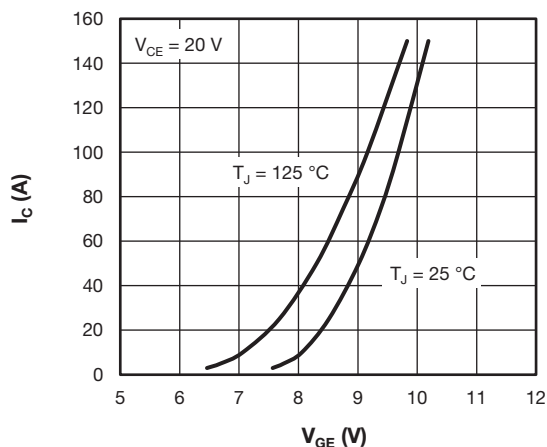


Fig. 4 - I_C vs V_{GE}
Typical Q1 to Q4 Trench IGBT Transfer Characteristics

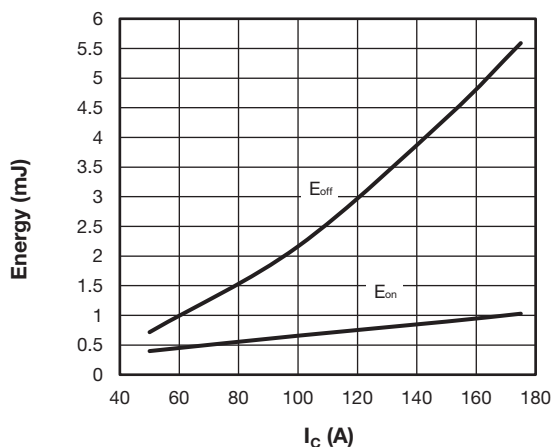


Fig. 7 - Energy Loss vs. I_C
(Typical Q1 - Q4 Trench IGBT Energy Loss vs. I_C
(with D5 - D6 Clamping Diode)),
 $T_J = 125^\circ\text{C}$, $V_{CC} = 325\text{ V}$, $R_g = 4.7\ \Omega$, $V_{GE} = \pm 15\text{ V}$, $L = 500\ \mu\text{H}$

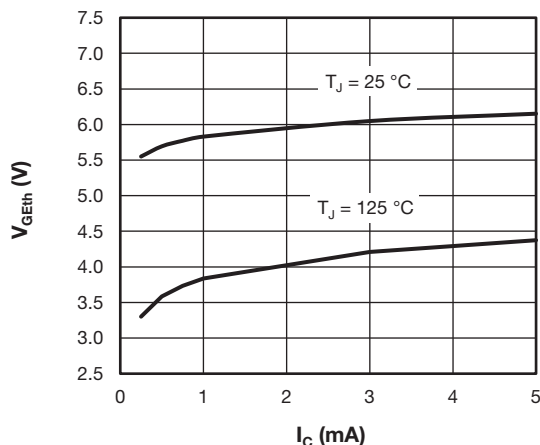


Fig. 5 - V_{GEth} vs. I_C
Typical Q1 to Q4 Trench IGBT Gate Threshold Voltage

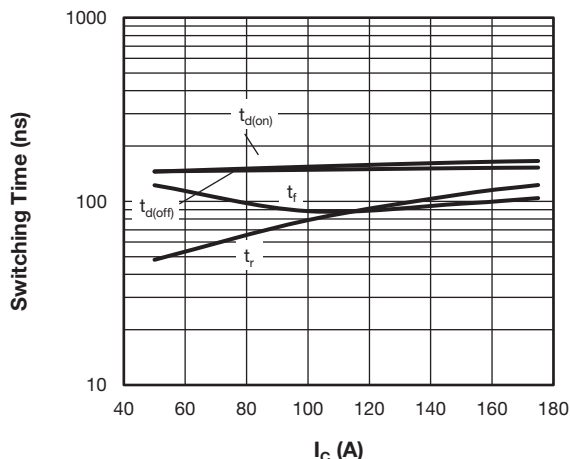


Fig. 8 - Switching Time vs. I_C
(Typical Q1 - Q4 Trench IGBT Switching Time vs. I_C
(with D5 - D6 Clamping Diode)),
 $T_J = 125^\circ\text{C}$, $V_{CC} = 325\text{ V}$, $R_g = 4.7\ \Omega$, $V_{GE} = \pm 15\text{ V}$, $L = 500\ \mu\text{H}$

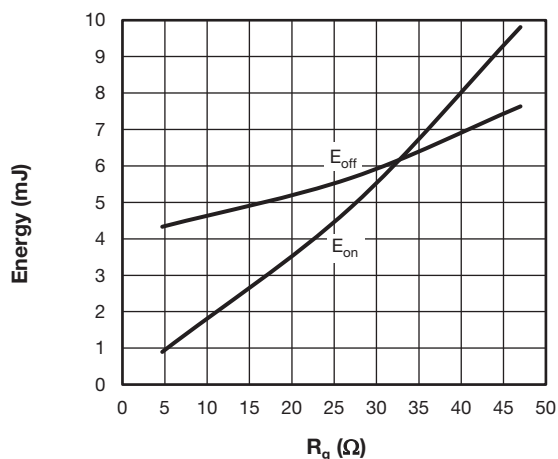


Fig. 9 - Energy Loss vs. R_g
(Typical Q1 - Q4 Trench IGBT Energy Loss vs. R_g
(with D5 - D6 Clamping Diode)),

$T_J = 125^\circ\text{C}$, $V_{CC} = 325\text{ V}$, $I_C = 150\text{ A}$, $V_{GE} = \pm 15\text{ V}$, $L = 500\text{ }\mu\text{H}$

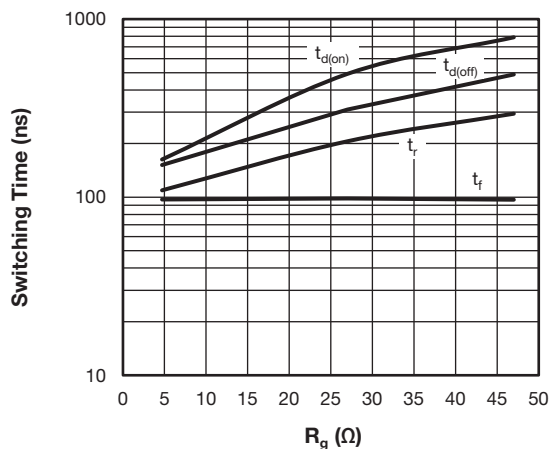


Fig. 10 - Switching Time vs. R_g
(Typical Q1 - Q4 Trench IGBT Switching Time vs. R_g
(with D5 - D6 Clamping Diode)),

$T_J = 125^\circ\text{C}$, $V_{CC} = 325\text{ V}$, $I_C = 150\text{ A}$, $V_{GE} = \pm 15\text{ V}$, $L = 500\text{ }\mu\text{H}$

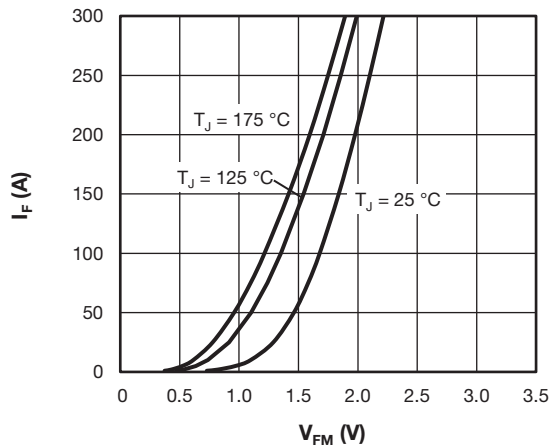


Fig. 11 - I_F vs. V_{FM}
(Typical D5 - D6 Clamping Diode Forward Characteristics)

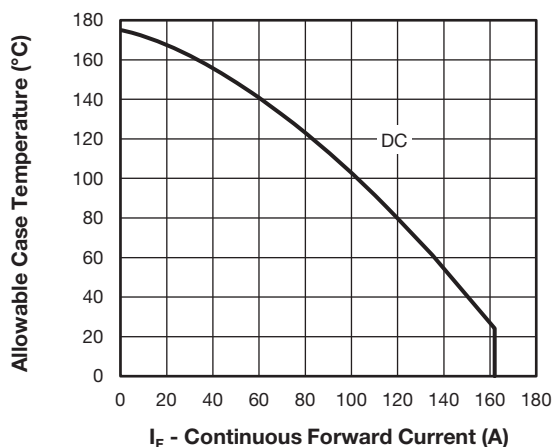


Fig. 12 - Allowable Case Temperature vs. Continuous Forward Current,
(Maximum D5 - D6 Diode Continuous Forward Current vs.
Case Temperature)

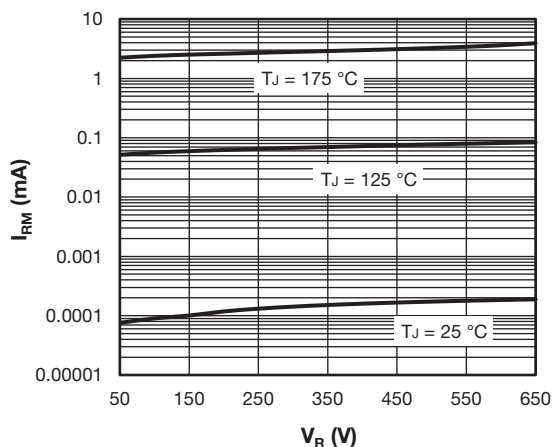


Fig. 13 - I_{RM} vs. V_R
(Typical D5 - D6 Clamping Diode Reverse Leakage Current)

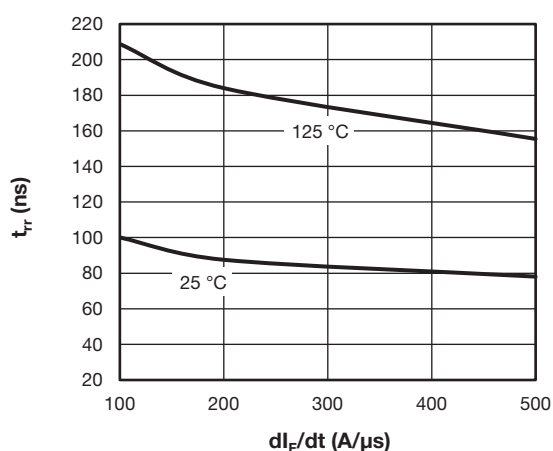


Fig. 14 - t_{rr} vs. dI_F/dt
(Typical D5 - D6 Clamping Diode Reverse Recovery Time vs. dI_F/dt),
 $V_{rr} = 200\text{ V}$, $I_F = 50\text{ A}$

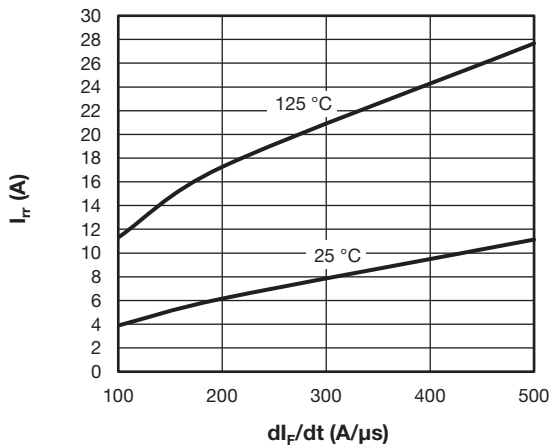


Fig. 15 - I_{rr} vs. dI_F/dt
(Typical D5 - D6 Clamping Diode Reverse Recovery Current vs. dI_F/dt), $V_{rr} = 200$ V, $I_F = 50$ A

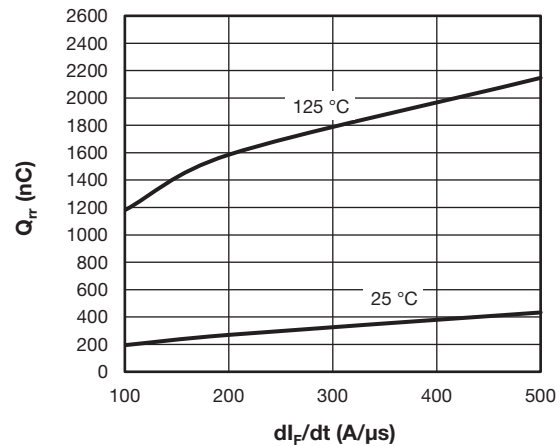


Fig. 16 - Q_{rr} vs. dI_F/dt
(Typical D5 - D6 Clamping Diode Reverse Recovery Charge vs. dI_F/dt), $V_{rr} = 200$ V, $I_F = 50$ A

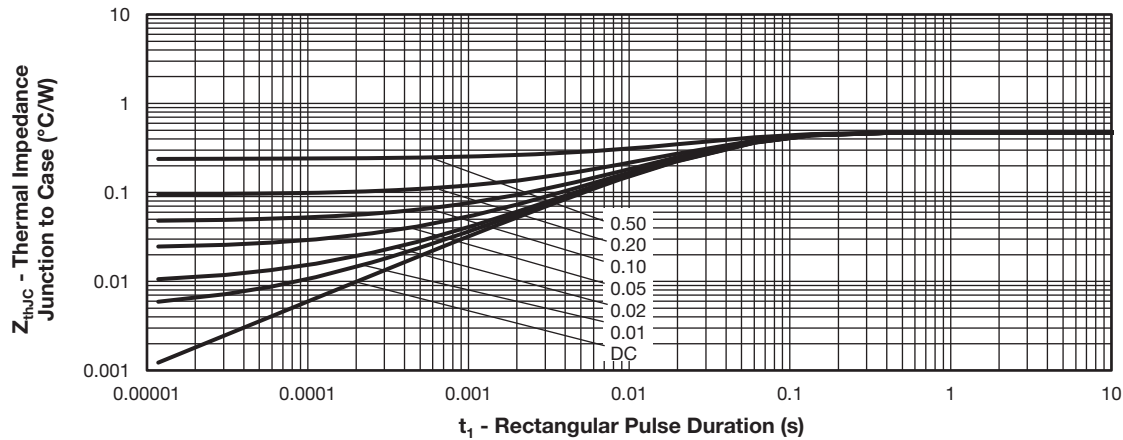


Fig. 17 - Z_{thJC} vs. t_1 Rectangular Pulse Duration (Maximum Thermal Impedance Z_{thJC} Characteristics - (D5 - D6 Clamping Diode))

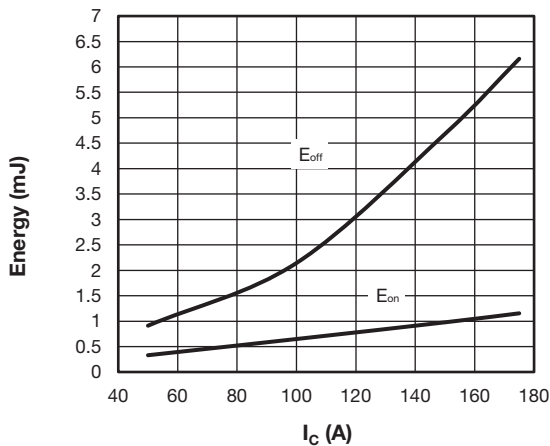


Fig. 18 - Energy Loss vs. I_C
(Typical Q2 - Q3 Trench IGBT Energy Loss vs. I_C
(with D2 - D3 Antiparallel Diode)),
 $T_J = 125$ °C, $V_{CC} = 325$ V, $R_g = 4.7$ Ω , $V_{GE} = \pm 15$ V, $L = 500$ μ H

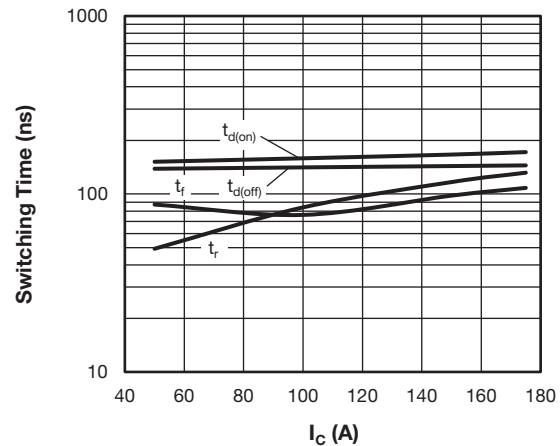


Fig. 19 - Switching Time vs. I_C
(Typical Q2 - Q3 Trench IGBT Switching Time vs. I_C
(with D2 - D3 Antiparallel Diode)),
 $T_J = 125$ °C, $V_{CC} = 325$ V, $R_g = 4.7$ Ω , $V_{GE} = \pm 15$ V, $L = 500$ μ H

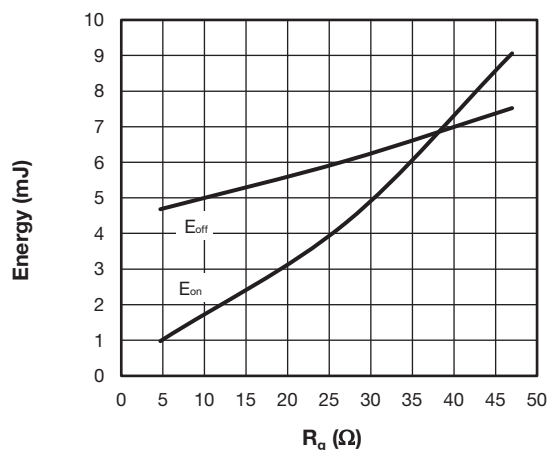


Fig. 20 - Energy Loss vs. R_g
(Typical Q2 - Q3 Trench IGBT Energy Loss vs. R_g
(with D2 - D3 Antiparallel Diode)),
 $T_J = 125^\circ\text{C}$, $V_{CC} = 325\text{ V}$, $I_C = 150\text{ A}$, $V_{GE} = \pm 15\text{ V}$, $L = 500\text{ }\mu\text{H}$

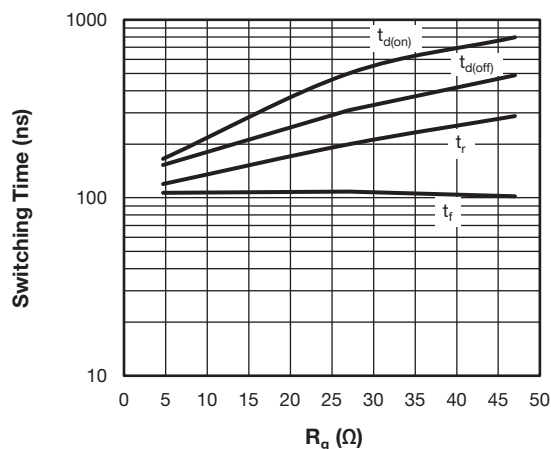


Fig. 21 - Switching Time vs. R_g (Typical Q2 - Q3 Trench IGBT
Switching Time vs. R_g (with D2 - D3 Antiparallel Diode)),
 $T_J = 125^\circ\text{C}$, $V_{CC} = 325\text{ V}$, $I_C = 150\text{ A}$, $V_{GE} = \pm 15\text{ V}$, $L = 500\text{ }\mu\text{H}$

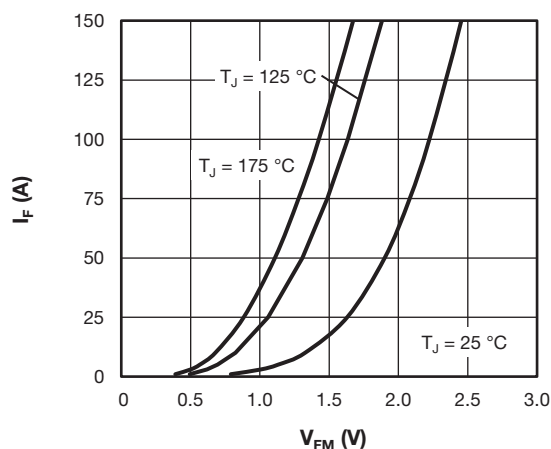


Fig. 22 - I_F vs. V_{FM}
(Typical D1 - D2 - D3 - D4 Antiparallel Diode Forward
Characteristics)

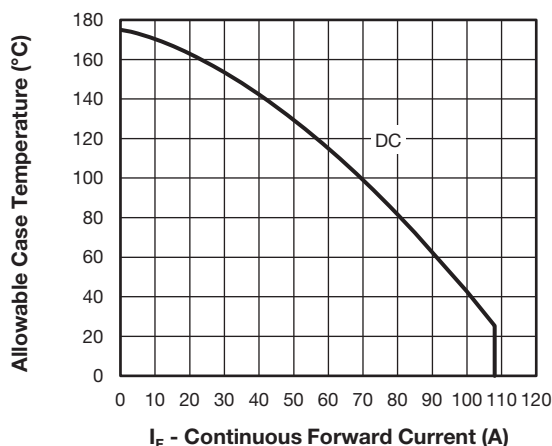


Fig. 23 - Allowable Case Temperature vs. Continuous Forward
Current,
(Maximum D1- D2 - D3 - D4 Diode Continuous Forward Current vs.
Case Temperature)

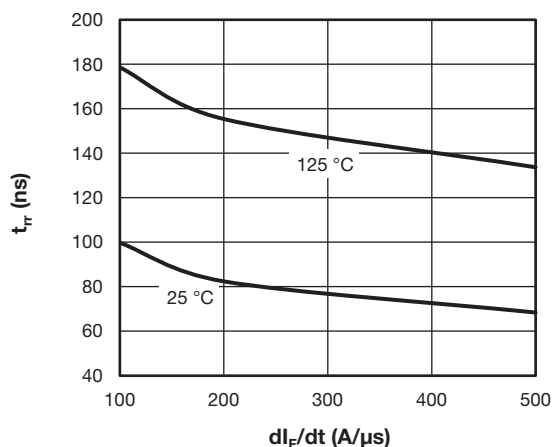


Fig. 24 - t_{rr} vs. dI_F/dt
(Typical D1 - D2 - D3 - D4 Antiparallel Diode Reverse Recovery Time
vs. dI_F/dt), $V_{rr} = 200\text{ V}$, $I_F = 50\text{ A}$

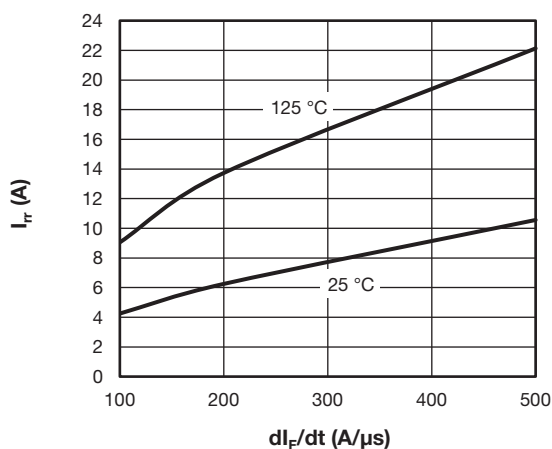


Fig. 25 - I_{rr} vs. dI_F/dt
(Typical D1 - D2 - D3 - D4 Antiparallel Diode Reverse Recovery
Current vs. dI_F/dt), $V_{rr} = 200\text{ V}$, $I_F = 50\text{ A}$

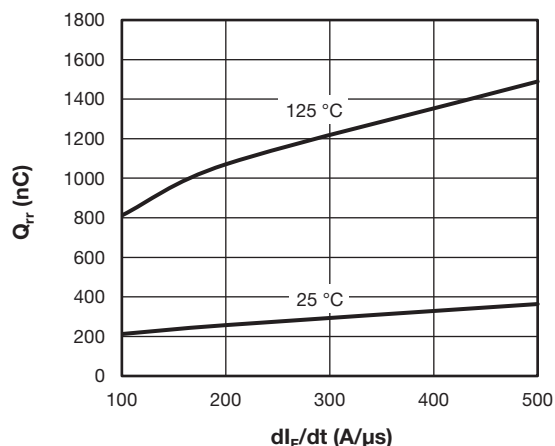


Fig. 26 - Q_{rr} vs. di_F/dt
(Typical D1 - D2 - D3 - D4 Antiparallel Diode Reverse Recovery Charge vs. di_F/dt), $V_{rr} = 200$ V, $I_F = 50$ A

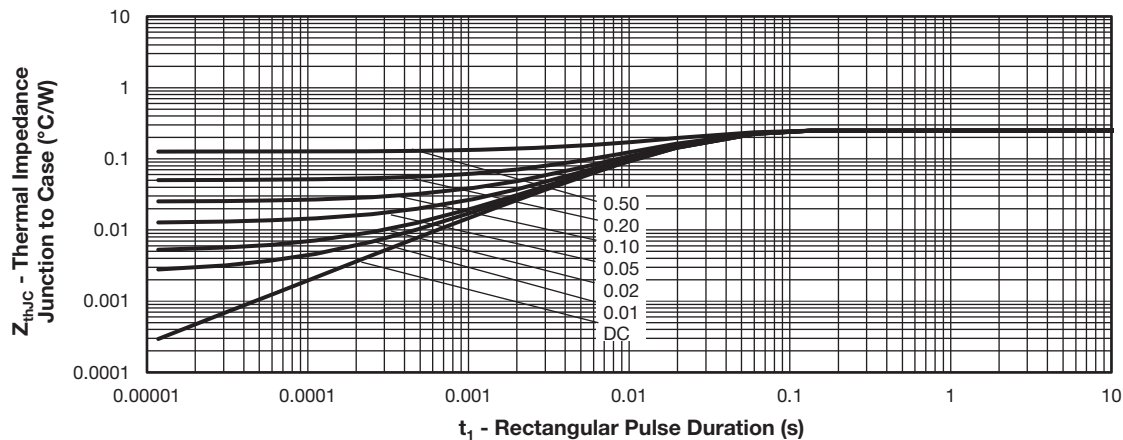


Fig. 27 - Z_{thJC} vs. t_1 Rectangular Pulse Duration (Maximum Thermal Impedance Z_{thJC} Characteristics - (Q2 - Q3 Trench IGBT))

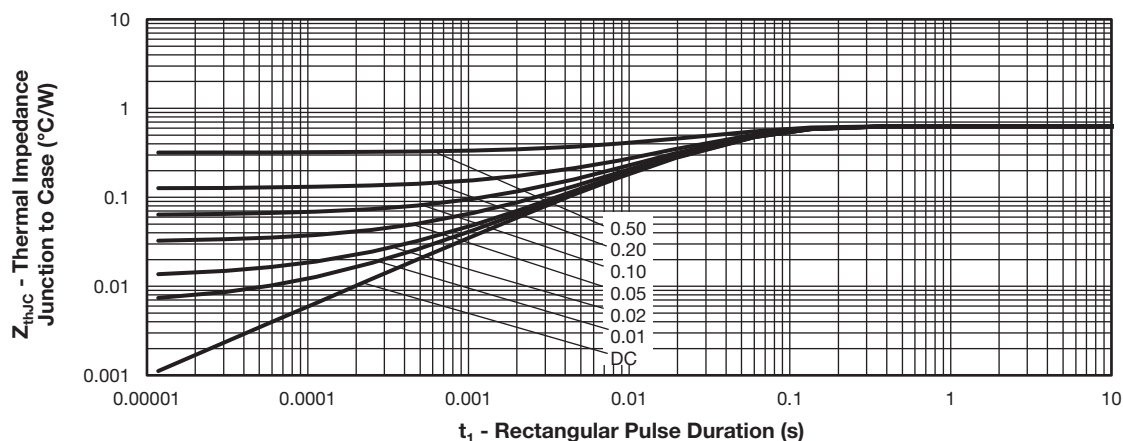


Fig. 28 - Z_{thJC} vs. t_1 Rectangular Pulse Duration (Maximum Thermal Impedance Z_{thJC} Characteristics - (D1 - D2 - D3 - D4 Antiparallel Diode))

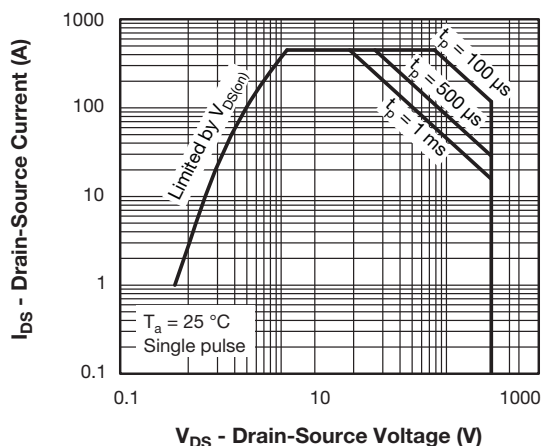


Fig. 29 - SOA

ORDERING INFORMATION TABLE

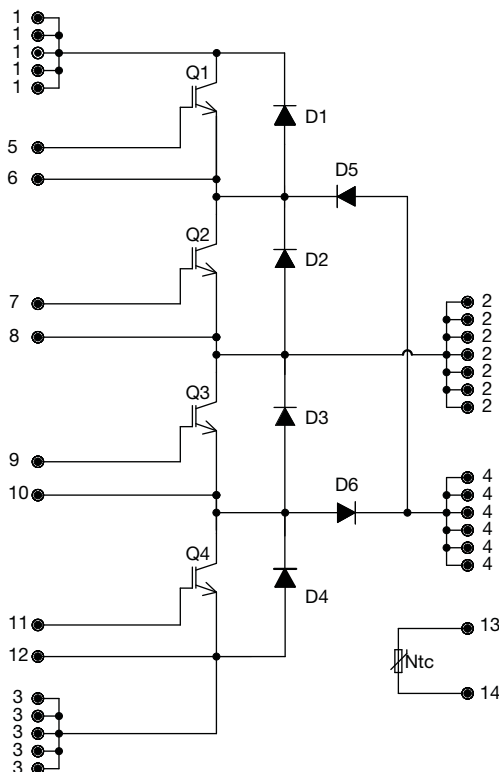
Device code

VS-	ET	F	150	Y	65	N
1	2	3	4	5	6	7

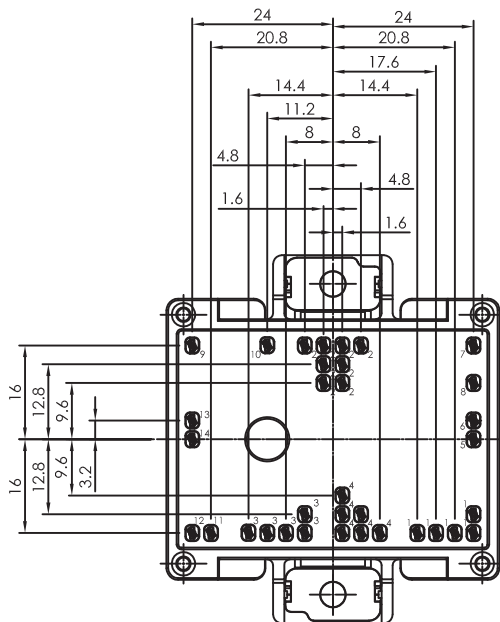
- 1** - Vishay Semiconductors product
- 2** - Package indicator (ET = EMIPAK 2B)
- 3** - Circuit configuration (F = 3-levels half bridge inverter stage)
- 4** - Current rating (150 = 150 A)
- 5** - Switch die technology (Y = trench IGBT)
- 6** - Voltage rating (65 = 650 V)
- 7** - Diode die technology (N = ultrafast diode)



CIRCUIT CONFIGURATION



PACKAGE in millimeters



LINKS TO RELATED DOCUMENTS

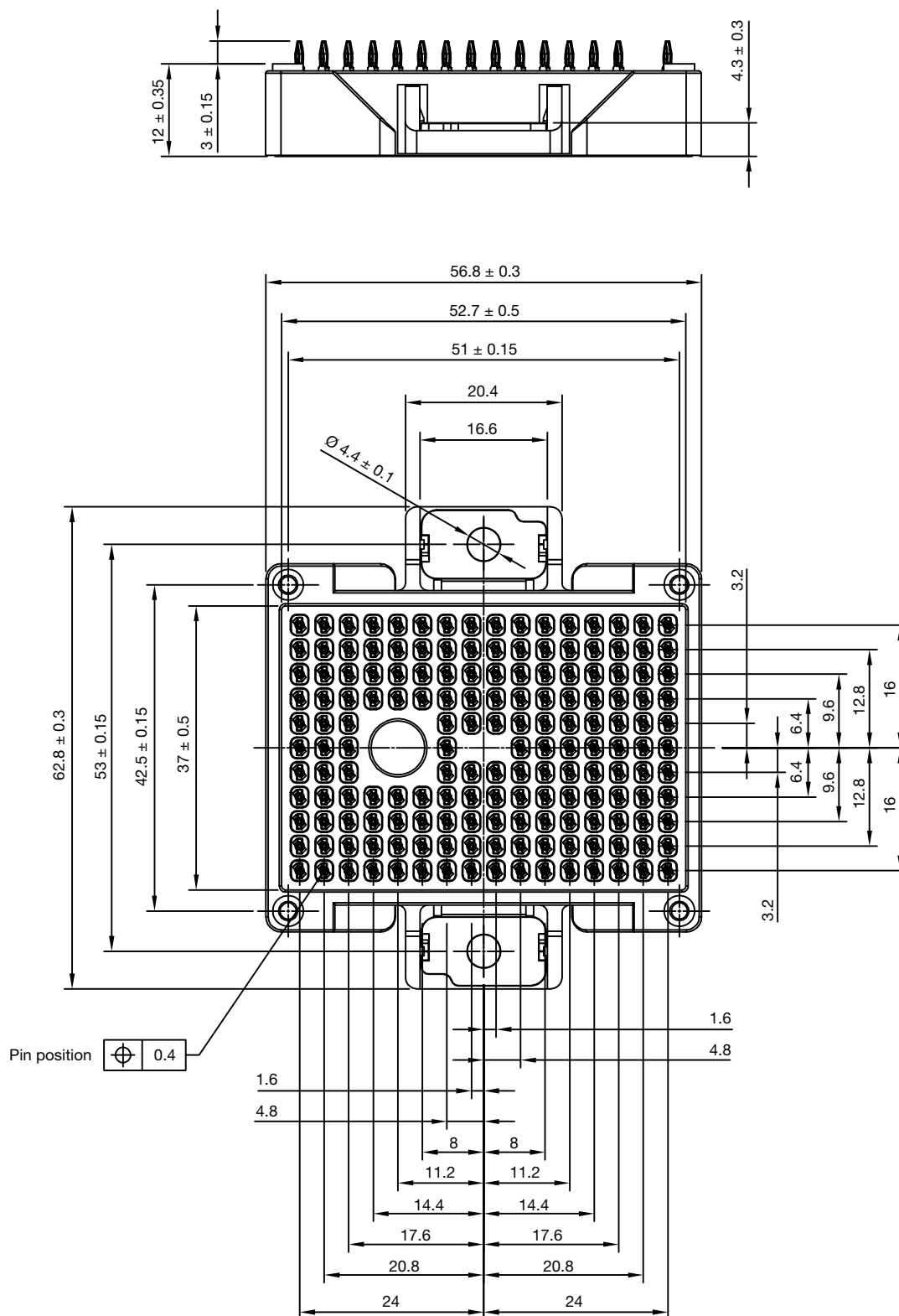
Dimensions

www.vishay.com/doc?95559



EMIPAK-2B PressFit

DIMENSIONS in millimeters





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